



Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A ferroelectric material for forming a ferroelectric that is described by a general formula ABO_3 , the ferroelectric material comprising lead zirconate titanate which constitutes an A-site compensation component which compensates for a vacancy of an A site, and a B-site compensation component which compensates for a vacancy of a B site-site,

wherein each of the A-site compensation component and the B-site compensation component comprises an oxide material including at least Si and Ge,

wherein the A-site compensation component includes an element which becomes divalent and an element which becomes trivalent, and

wherein the B-site compensation component includes an element which becomes pentavalent.

2-4. (Canceled)

5. (Currently Amended) The ferroelectric material as defined in ~~claim 3~~, claim 1, wherein a lanthanoid series element is added as the element which becomes a trivalent state.

6. (Canceled)

7. (Withdrawn) A method of manufacturing a ferroelectric film, comprising using the ferroelectric material as defined in claim 1.

8. (Withdrawn) The method of manufacturing a ferroelectric film as defined in claim 7, comprising:

forming a ferroelectric material film by stacking a plurality of raw material layers using the ferroelectric material; and

performing a heat treatment for forming initial crystal nuclei in each of the raw material layers.

9. (Withdrawn) The method of manufacturing a ferroelectric film as defined in claim 8,

wherein the heat treatment is performed by using a rapid thermal annealing method.

10. (Withdrawn) The method of manufacturing a ferroelectric film as defined in claim 7,

wherein the ferroelectric film is formed by crystallizing the ferroelectric material film by applying a heat treatment to the ferroelectric material film.

11. (Withdrawn) A method of manufacturing a ferroelectric capacitor including forming a lower electrode, a ferroelectric film and an upper electrode on a base, the method comprising:

forming a ferroelectric material film by stacking a plurality of raw material layers using the ferroelectric material as defined in claim 1; and

performing a heat treatment for forming initial crystal nuclei in each of the raw material layers.

12. (Withdrawn) The method of manufacturing a ferroelectric capacitor as defined in claim 11,

wherein the heat treatment is performed by using a rapid thermal annealing method.

13. (Withdrawn) The method of manufacturing a ferroelectric capacitor as defined in claim 11,

wherein the ferroelectric film is formed by crystallizing the ferroelectric material film by applying a heat treatment to the ferroelectric material film.

14. (Withdrawn) A ferroelectric capacitor manufactured by using the method of manufacturing a ferroelectric capacitor as defined in claim 11.

15. (Withdrawn) A ferroelectric memory comprising the ferroelectric capacitor as defined in claim 14.

16. (Withdrawn) A piezoelectric device comprising the ferroelectric capacitor as defined in claim 14.